TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

# SM12GZ47,SM12JZ47,SM12GZ47A,SM12JZ47A

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### AC POWER CONTROL APPLICATIONS

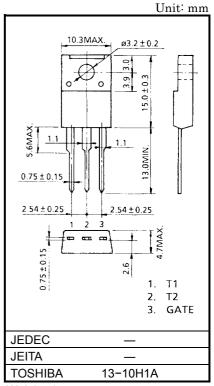
Repetitive Peak off-State Voltage : V<sub>DRM</sub> = 400, 600V
 R.M.S On-State Current : I<sub>T</sub> (RMS) = 12A

High Commutating (dv / dt)

• Isolation Voltage :  $V_{Isol} = 1500V AC$ 

### **MAXIMUM RATINGS**

CHARACTERI	STIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and	SM12GZ47 SM12GZ47A	Vanu	400	٧	
Repetitive Peak Reverse Voltage	SM12JZ47 SM12JZ47A	$V_{DRM}$	600		
R. M. S. On-tate Currer (Full Sine Waveform TC		I <sub>T (RMS)</sub>	12	Α	
Peak One Cylce Surge On-State		l=a	120 (50Hz)	Α	
Current (Non-Repetitive	e)	ITSM	132 (60Hz)	^	
I <sup>2</sup> t Limit Value		ı²t	72	A <sup>2</sup> s	
Critical Rate of Rise of C Current	On-State (Note 1)	di / dt	50	A / μs	
Peak Gate Power Dissip	ation	$P_{GM}$	5	W	
Average Gate Power Dis	ssipation	P <sub>G (AV)</sub>	0.5	W	
Peak Gate Voltage		$V_{FGM}$	10	V	
Peak Gate Current		$I_{GM}$	2	Α	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature R	ange	T <sub>stg</sub>	-40~125	°C	
Isolation Voltage (AC, t	= 1min.)	V <sub>Isol</sub>	1500	V	



Weight: 1.7g

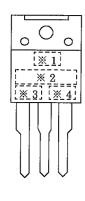
Note 1: di / dt test condition  $V_{DRM} = 0.5 \times Rated$   $I_{TM} \le 17A$   $t_{gw} \ge 10\mu s$   $t_{gr} \le 250ns$   $i_{gp} = I_{GT} \times 2.0$ 



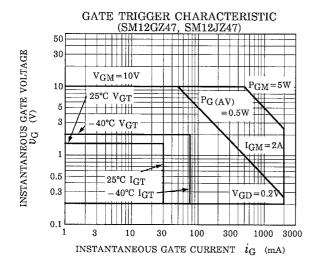
## **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

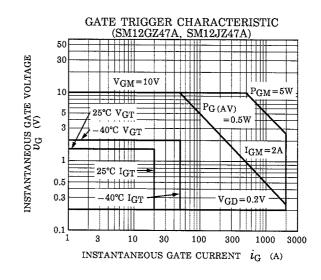
CHARACTERISTIC			SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT	
Repetitive Peak	Off-Sta	State Current I <sub>DRM</sub> V <sub>DRM</sub> = Rated				_	_	20	μA	
Gate Trigger Voltage  II  III  IV		I		V <sub>D</sub> = 12V,	T2 (+) , Gate (+)	-	_	1.5	V	
		II			T2 (+) , Gate (-)	_	_	1.5		
		III	$V_{GT}$	$R_L = 20\Omega$	T2 (-) , Gate (-)	-	_	1.5		
		IV			T2 (-) , Gate (+)	-	_	_		
						T2 (+) , Gate (+)	-	_	30	
	SM12	SM12GZ47 SM12JZ47	П			T2 (+) , Gate (-)	_	_	30	
	SM12		III			T2 (-) , Gate (-)	_	_	30	
Gate Trigger					V <sub>D</sub> = 12V,	T2 (-) , Gate (+)	_	_	_	
Current		SM12GZ47A SM12JZ47A	I	I <sub>GT</sub>	R <sub>L</sub> = 20Ω	T2 (+) , Gate (+)	_	_	20	mA
	SM12		П			T2 (+) , Gate (-)	_	_	20	
	SM12		III			T2 (-) , Gate (-)	_	_	20	
				•		T2 (-) , Gate (+)	-	_	_	
Peak On-State Voltage		V <sub>TM</sub>	I <sub>TM</sub> = 17A		_	_	1.5	V		
Gate Non-Trigger Voltage		$V_{GD}$	V <sub>D</sub> = Rated, Tc = 125°C		0.2	_	_	V		
Holding Current		lн	V <sub>D</sub> = 12V, I <sub>TM</sub> = 1A			_	50	mA		
Thermal Resistance		R <sub>th (j-c)</sub>	Junction to Case, AC			_	3.0	°C/W		
Critical Rate of		SM12GZ47 SM12JZ47		dv / dt	V <sub>DRM</sub> = Rated, T <sub>i</sub> = 125°C		_	300	_	· V/μs
Rise of Off-State Voltage	<del>-</del>	SM12GZ47 SM12JZ47		uv / ut	Exponential Rise		_	200	_	ν/μδ
Critical Rate of Rise of Off-State	9	SM12GZ47 SM12JZ47		(dv / dt) -	V <sub>DRM</sub> = 400V, T <sub>j</sub> = 125°C		10	_	_	V / 110
Voltage at Commutation		SM12GZ47 SM12JZ47		(dv / dt) c	(di / dt) c = -6.5A / ms		4	_	_	- V / μs

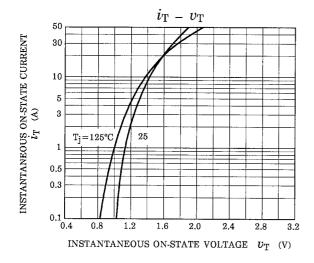
### **MARKING**

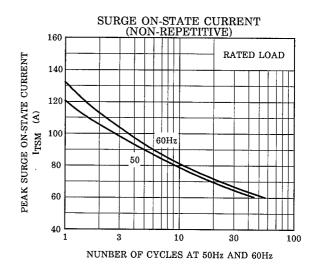


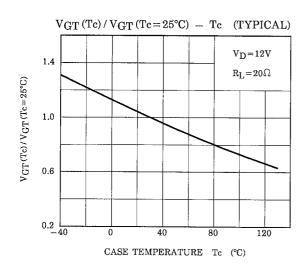
*NUMBE	ER		MARK		
*1		TOSHIBA PRODUCT MARK		7	
*2		SM12GZ47, SM12GZ47A	M12GZ47		
	TYPE	SM12JZ47, SM12JZ47A	M12JZ47		
*3			SM12GZ47A, SM12JZ47A	А	
*4			(Starting from Alphabet A) (Last Decimal Digit of the Current Year)	Example 8A: January 1998 8B: February 1998 8L: December 1998	

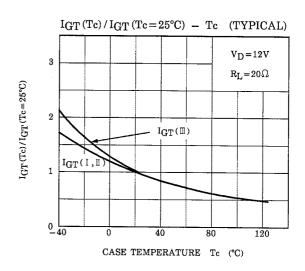


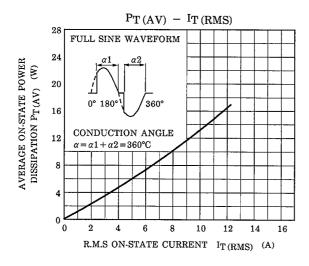


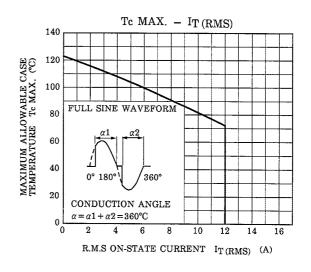


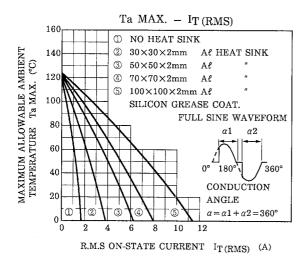


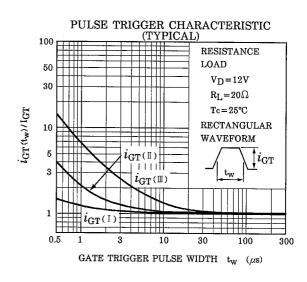


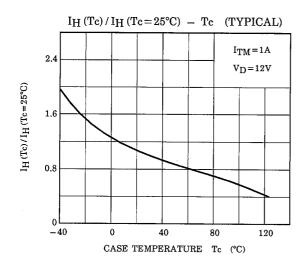


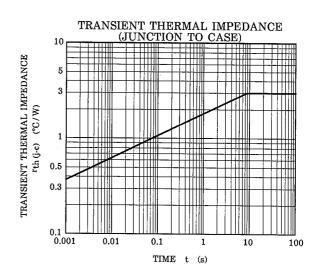












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